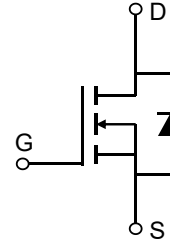


Description

Features

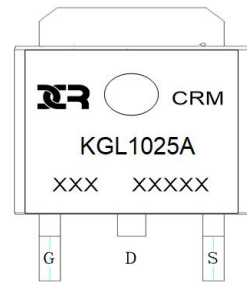
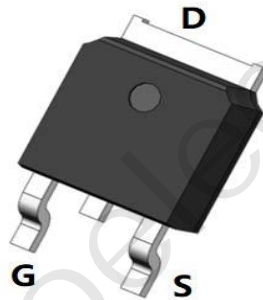
- 100V, 30A
 $R_{DS(ON)}$ Typ = 20mΩ @ $V_{GS} = 10V$
 $R_{DS(ON)}$ Typ = 25mΩ @ $V_{GS} = 4.5V$
- Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔV_{ds} TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMKGL1025A	CRMKGL1025A	TO-252-3L	TAPING	13"	2500	25000

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	A
I_{DM}	Pulsed Drain Current ⁽¹⁾	120	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	30	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	°C

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	1	1.8	2.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽³⁾	$V_{GS} = 10\text{V}$, $I_D = 10\text{A}$	-	20	26	mΩ
		$V_{GS} = 4.5\text{V}$, $I_D = 8\text{A}$	-	25	32.5	mΩ

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 50\text{V}$, $f = 1\text{MHz}$	-	650	-	pF
C_{oss}	Output Capacitance		-	279	-	pF
C_{rss}	Reverse Transfer Capacitance		-	11	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to 10V $V_{DS} = 50\text{V}$, $I_D = 10\text{A}$	-	25	-	nC
Q_{gs}	Gate Source Charge		-	6	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	5	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}$, $V_{DD} = 50\text{V}$ $I_D = 10\text{A}$, $R_{GEN} = 3\Omega$	-	14	-	ns
t_r	Turn-On Rise Time		-	12	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	23	-	ns
t_f	Turn-Off Fall Time		-	6	-	ns

Drain-Source Diode Characteristics and Max Ratings

I_S	Maximum Continuous Drain to Source Diode Forward Current	$V_{GS} = 0\text{V}$, $I_S = 10\text{A}$	-	-	30	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	120	A
V_{SD}	Drain to Source Diode Forward Voltage		-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time		-	50	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	90	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 50\text{V}$, $V_G = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 0.5\text{mH}$, $I_{AS} = 11\text{A}$
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Performance Characteristics

Figure 1: Output Characteristics

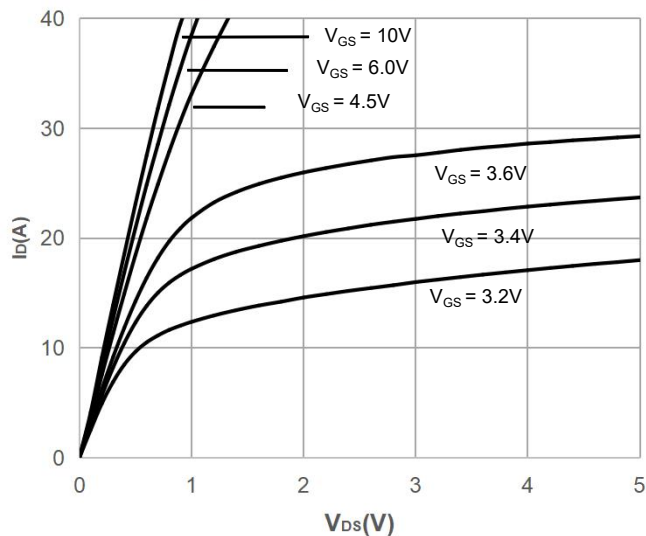


Figure 2: Typical Transfer Characteristics

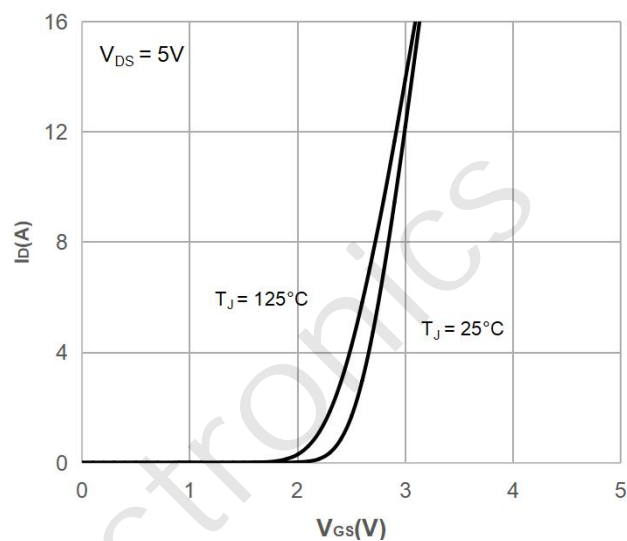


Figure 3: On-resistance vs. Drain Current

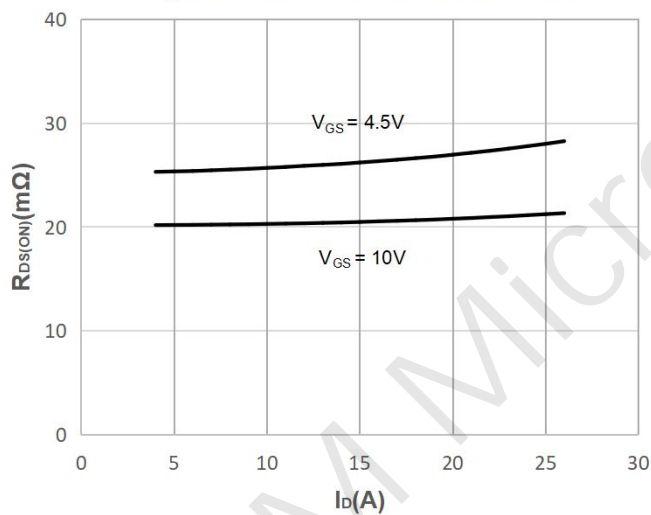


Figure 4: Body Diode Characteristics

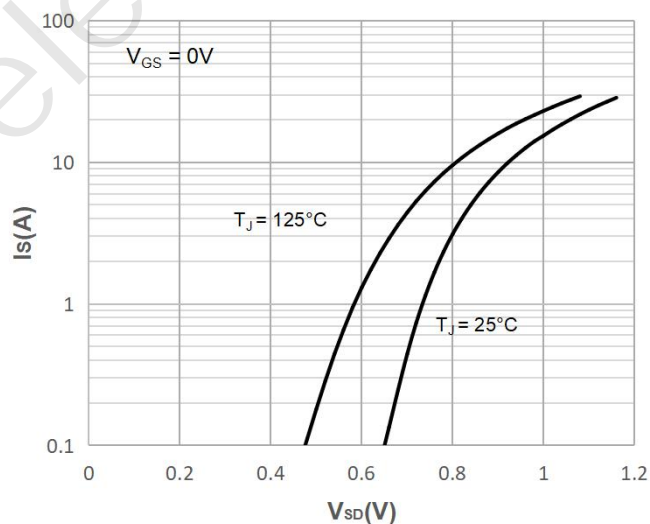


Figure 5: Gate Charge Characteristics

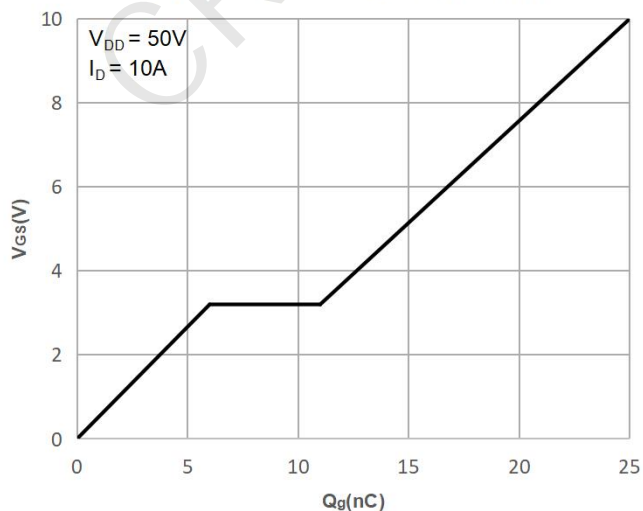
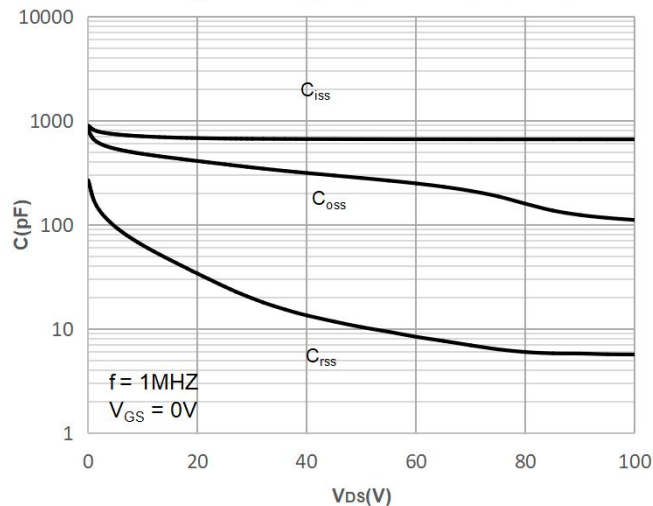


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

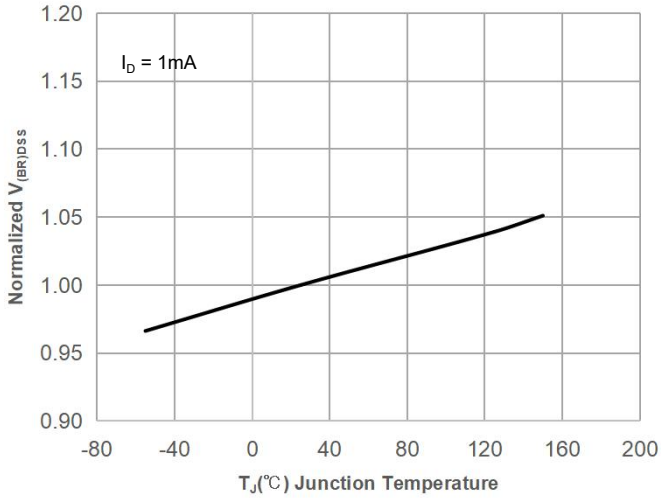


Figure 8: Normalized on Resistance vs. Junction Temperature

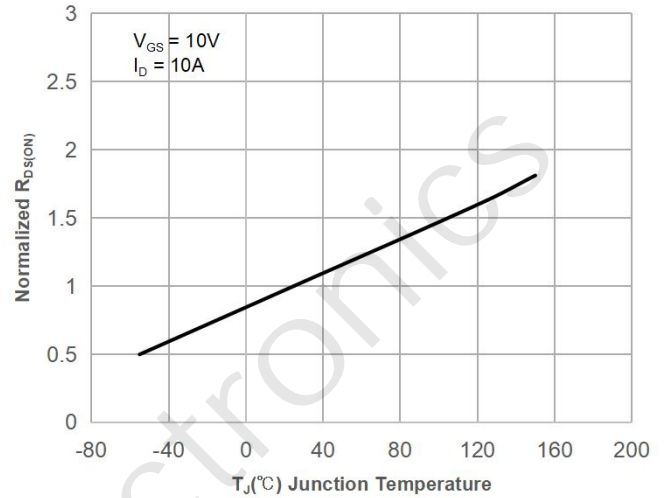


Figure 9: Maximum Safe Operating Area

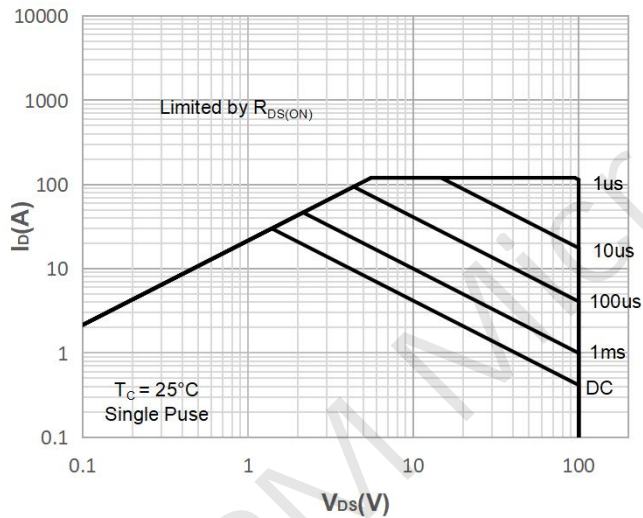


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

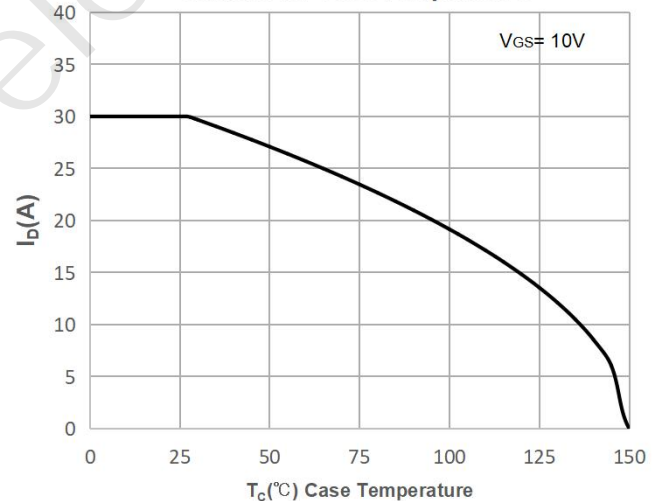


Figure 11: Normalized Maximum Transient Thermal Impedance

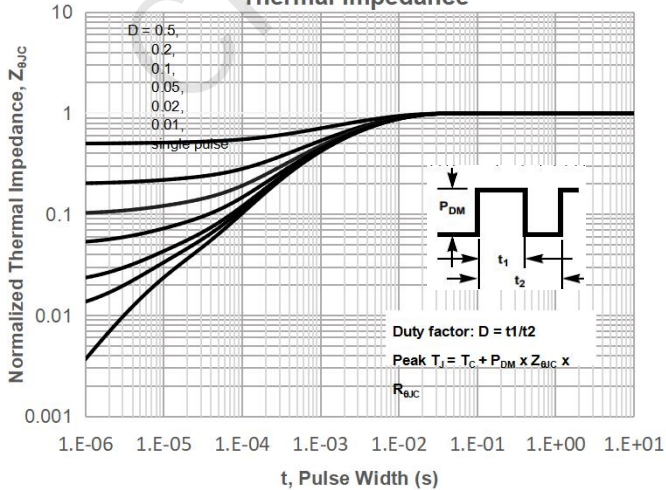
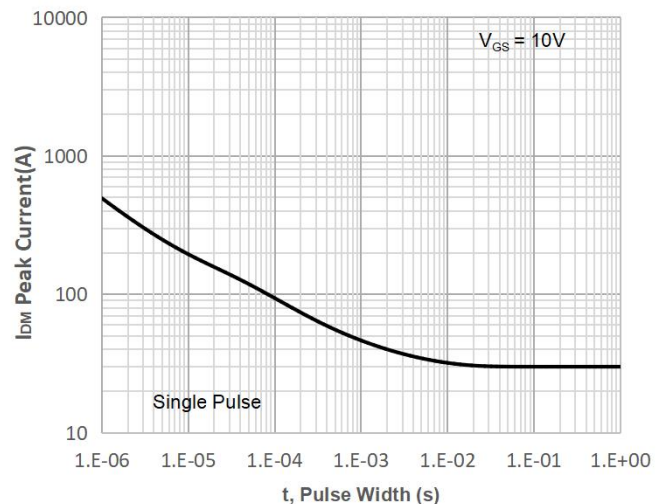


Figure 12: Peak Current Capacity



Test Circuit

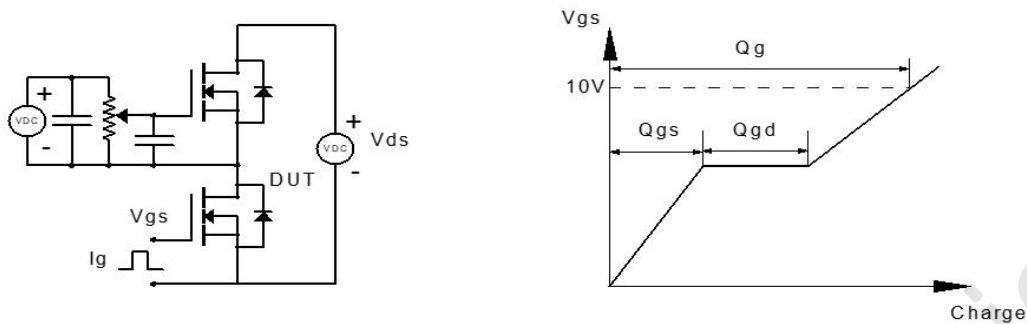


Figure 1: Gate Charge Test Circuit & Waveform

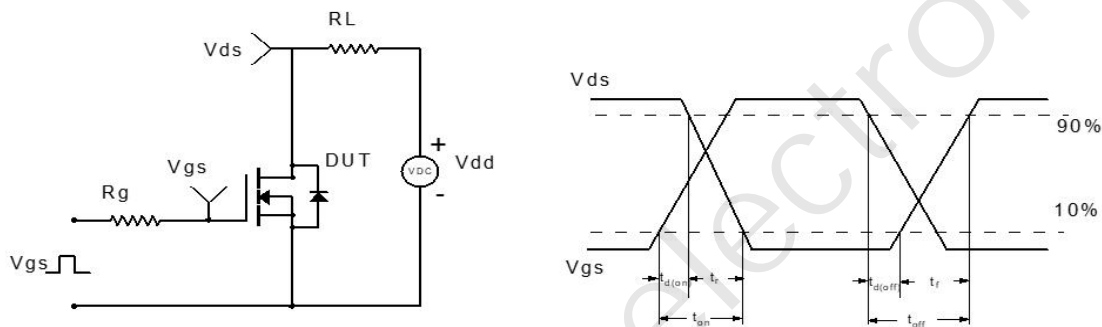


Figure 2: Resistive Switching Test Circuit & Waveform

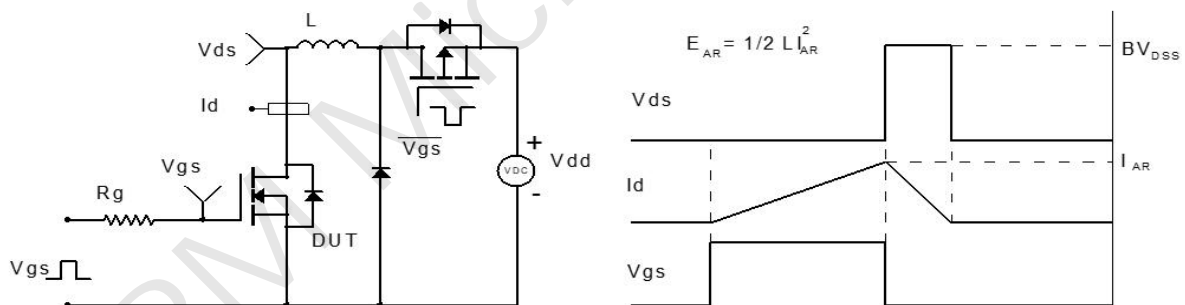


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

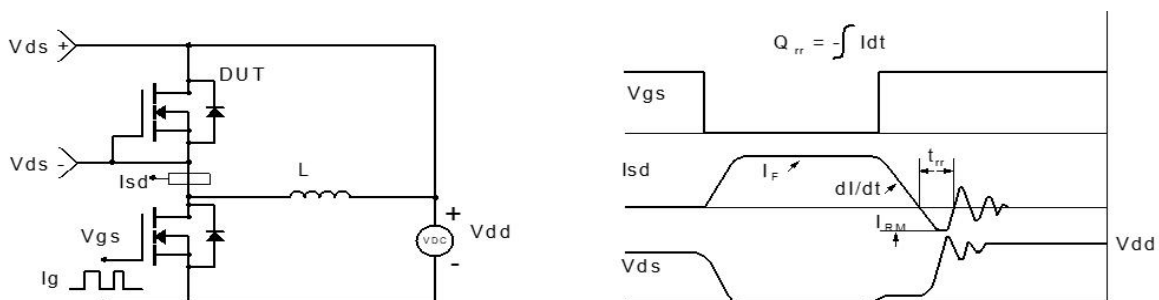
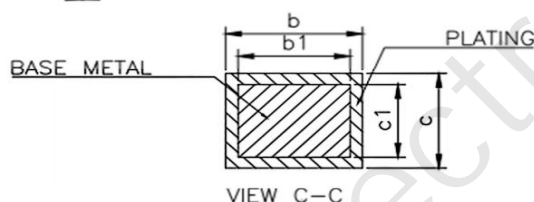
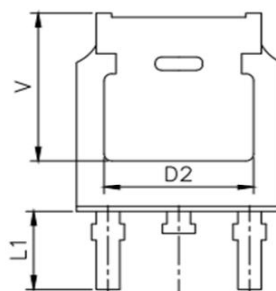
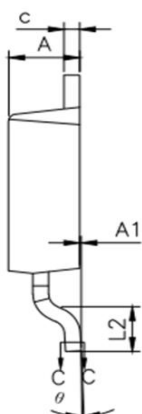
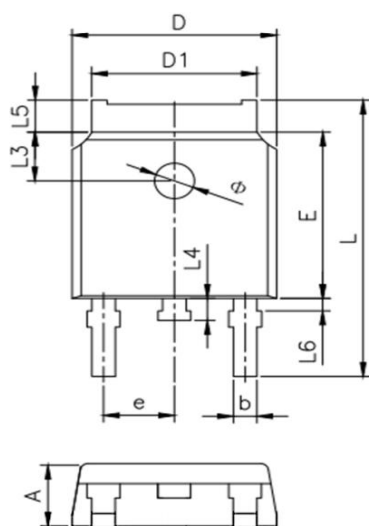


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-252-3L)




SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	—	0.127
b	0.66	—	0.86
b1	0.65	0.76	0.81
D	6.50	6.60	6.70
D1	5.10	5.33	5.46
c	0.47	—	0.60
c1	0.46	0.51	0.56
D2	4.83 REF.		
E	6.00	6.10	6.20
e	2.186	2.286	2.386
L	9.80	10.10	10.40
L1	2.90 REF.		
L2	1.40	1.50	1.60
L3	1.80 REF.		
L4	0.60	0.80	1.00
L5	0.90	—	1.25
L6	0.15	—	0.75
Φ	1.10	—	1.30
θ	0°	—	8°
V	5.40 REF.		

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